

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

2SK3471

Switching Regulator and DC-DC Converter Applications

- Low drain-source ON resistance: $R_{DS(ON)} = 10 \Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 0.4 \text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = 100 \mu\text{A}$ (max) ($V_{DS} = 500 \text{ V}$)
- Enhancement-model: $V_{th} = 2.0 \text{ to } 4.0 \text{ V}$ ($V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$)

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	500	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	500	V
Gate-source voltage		V_{GSS}	± 30	V
Drain current	DC (Note 1)	I_D	0.5	A
	Pulse (Note 1)	I_{DP}	1.5	
Drain power dissipation		P_D	0.5	W
Drain power dissipation (Note 2)		P_D	1.5	W
Single pulse avalanche energy (Note 3)		E_{AS}	14.3	mJ
Avalanche current		I_{AR}	0.5	A
Repetitive avalanche energy (Note 4)		E_{AR}	0.05	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	250	$^\circ\text{C/W}$

Note 1: Please use devices on condition that the channel temperature is below 150°C .

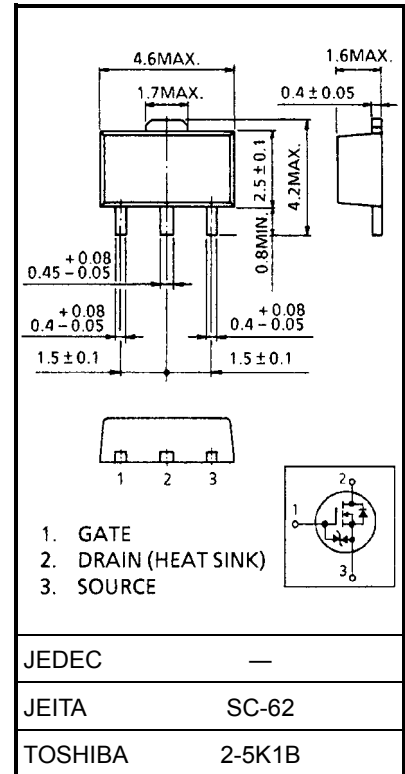
Note 2: Mounted on ceramic substrate ($25.4 \text{ mm} \times 25.4 \text{ mm} \times 0.8 \text{ mm}$)

Note 3: $V_{DD} = 90 \text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 100 \text{ mH}$, $R_G = 25 \Omega$, $I_{AR} = 0.5 \text{ A}$

Note 4: Repetitive rating: Pulse width limited by maximum channel temperature

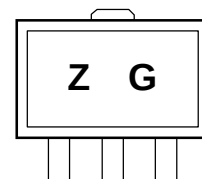
This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm



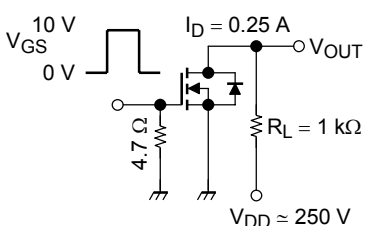
Weight: 0.05 g (typ.)

Marking



(The two digits represent the part number.)

Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Drain-source breakdown voltage		$V_{(BR)GSS}$	$I_G = \pm 10 \mu\text{A}, V_{DS} = 0 \text{ V}$	± 30	—	—	V
Drain cut-OFF current		I_{DSS}	$V_{DS} = 500 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	500	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	2.0	—	4.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 0.25 \text{ A}$	—	10	18	Ω
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 0.25 \text{ A}$	0.2	0.4	—	S
Input capacitance		C_{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	75	—	pF
Reverse transfer capacitance		C_{rss}		—	7	—	
Output capacitance		C_{oss}		—	24	—	
Switching time	Rise time	t_r	 $V_{GS} = 10 \text{ V}$ 0 V $I_D = 0.25 \text{ A}$ V_{OUT} 4.7Ω $R_L = 1 \text{ k}\Omega$ $V_{DD} \approx 250 \text{ V}$ Duty $\leq 1\%$, $t_w = 10 \mu\text{s}$	—	11	—	ns
	Turn-ON time	t_{on}		—	18	—	
	Fall time	t_f		—	54	—	
	Turn-OFF time	t_{off}		—	95	—	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 0.5 \text{ A}$	—	3.8	—	nC
Gate-source charge		Q_{gs}		—	1.9	—	
Gate-drain ("miller") charge		Q_{gd}		—	1.9	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	0.5	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	1.5	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 0.5 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	−1.5	V
Reverse recovery time	t_{rr}	$I_{DR} = 0.5 \text{ A}, V_{GS} = 0 \text{ V},$	—	190	—	ns
Reverse recovery charge	Q_{rr}	$dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$	—	380	—	nC

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